NSN 5961-00-051-8097

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-051-8097 **Inclosure Material:** Metal **Overall Length:** 0.350 inches **Overall Diameter:** 0.875 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 300.0 breakover voltage, dc **Current Rating Per Characteristic:** 25.00 amperes source cutoff current **Power Rating Per Characteristic:** 0.5 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Internal junction configuration arrangement pnpn **Terminal Type And Quantity:** 3 tab, solder lug **Specification Data:** 80131-release3983 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0